Osamu Nakatsuka

List of Publications by Year
in descending order

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250	3,131	201385	214527
papers	citations	27 h-index	47 g-index

252	252	252	2159
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	High resolution-high energy x-ray photoelectron spectroscopy using third-generation synchrotron radiation source, and its application to Si-high k insulator systems. Applied Physics Letters, 2003, 83, 1005-1007.	1.5	351
2	Growth and applications of GeSn-related group-IV semiconductor materials. Science and Technology of Advanced Materials, 2015, 16, 043502.	2.8	144
3	Growth of highly strain-relaxed Ge1âˆ'xSnx/virtual Ge by a Sn precipitation controlled compositionally step-graded method. Applied Physics Letters, 2008, 92, .	1.5	112
4	Characterization of GeSn materials for future Ge pMOSFETs source/drain stressors. Microelectronic Engineering, 2011, 88, 342-346.	1.1	103
5	Ferromagnetism and Electronic Structures of Nonstoichiometric Heusler-Alloy<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>Fe</mml:mi><mml:mrow><mml:mn>3</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi> Grown on Ge(111). Physical Review Letters, 2009, 102, 137204.	2.9	94
6	Mobility Behavior of Ge_{1-x}Sn_xLayers Grown on Silicon-on-Insulator Substrates. Japanese Journal of Applied Physics, 2010, 49, 04DA10.	0.8	81
7	Development of Ni/Al and Ni/Ti/Al ohmic contact materials for p-type 4H-SiC. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 98, 286-293.	1.7	72
8	Growth and structure evaluation of strain-relaxed Ge1âˆ'xSnxbuffer layers grown on various types of substrates. Semiconductor Science and Technology, 2007, 22, S231-S235.	1.0	70
9	Low temperature growth of Ge1âˆ'Sn buffer layers for tensileâ€"strained Ge layers. Thin Solid Films, 2010, 518, S2-S5.	0.8	69
10	High hole mobility tin-doped polycrystalline germanium layers formed on insulating substrates by low-temperature solid-phase crystallization. Applied Physics Letters, 2015, 107, .	1.5	64
11	Pure-edge dislocation network for strain-relaxed SiGeâˆ•Si(001) systems. Applied Physics Letters, 2005, 86, 221916.	1.5	58
12	Improvement in NiSi/Si contact properties with C-implantation. Microelectronic Engineering, 2005, 82, 479-484.	1.1	55
13	Low Resistance TiAl Ohmic Contacts with Multi-Layered Structure for p-Type 4H-SiC. Materials Transactions, 2002, 43, 1684-1688.	0.4	43
14	Crystalline orientation dependence of electrical properties of Mn Germanide/Ge(1 1 1) and (0 0 1) Schottky contacts. Microelectronic Engineering, 2011, 88, 605-609.	1.1	42
15	Tensile strained Ge layers on strain-relaxed Ge1âˆ'Sn /virtual Ge substrates. Thin Solid Films, 2008, 517, 159-162.	0.8	41
16	Large grain growth of Ge-rich Ge1âˆ'xSnx(xâ€‰â‰ˆâ€‰0.02) on insulating surfaces using pulsed laser annealing in flowing water. Applied Physics Letters, 2014, 104, 061901.	1.5	37
17	Electrical Properties and Solid-Phase Reactions in Ni/Si(100) Contacts. Japanese Journal of Applied Physics, 2002, 41, 2450-2454.	0.8	36
18	Interfacial reaction and electrical properties in Ni/Si and Ni/SiGe(C) contacts. Applied Surface Science, 2004, 224, 215-221.	3.1	36

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19	Ge1â^'Sn stressors for strained-Ge CMOS. Solid-State Electronics, 2011, 60, 53-57.	0.8	33
20	Molecular beam deposition of Al2O3 on p-Ge(001)/Ge0.95Sn0.05 heterostructure and impact of a Ge-cap interfacial layer. Applied Physics Letters, 2011, 98, .	1.5	33
21	Near-infrared light absorption by polycrystalline SiSn alloys grown on insulating layers. Applied Physics Letters, 2015, 106, .	1.5	33
22	Growth of Ge1â^'xSnx heteroepitaxial layers with very high Sn contents on InP(001) substrates. Thin Solid Films, 2012, 520, 3201-3205.	0.8	32
23	Low-Temperature Formation of Epitaxial NiSi2Layers with Solid-Phase Reaction in Ni/Ti/Si(001) Systems. Japanese Journal of Applied Physics, 2005, 44, 2945-2947.	0.8	30
24	Realizing High Thermoelectric Performance at Ambient Temperature by Ternary Alloying in Polycrystalline Si1-x-yGexSny Thin Films with Boron Ion Implantation. Scientific Reports, 2019, 9, 14342.	1.6	30
25	Formation of Ni(Ge1â^'xSnx) layers with solid-phase reaction in Ni/Ge1â^'xSnx/Ge systems. Solid-State Electronics, 2011, 60, 46-52.	0.8	29
26	Operation of inverter and ring oscillator of ultrathin-body poly-Ge CMOS. Applied Physics Express, 2014, 7, 121302.	1.1	29
27	Liquid-Sn-driven lateral growth of poly-GeSn on insulator assisted by surface oxide layer. Applied Physics Letters, 2013, 103, .	1.5	28
28	Local strain in SiGe/Si heterostructures analyzed by X-ray microdiffraction. Thin Solid Films, 2006, 508, 128-131.	0.8	27
29	Plasma surface treatment of polymers with inductivity-coupled RF plasmas driven by low-inductance antenna units. Thin Solid Films, 2009, 518, 1006-1011.	0.8	26
30	Control of Sn Precipitation and Strain Relaxation in Compositionally Step-Graded Ge1-xSnxBuffer Layers for Tensile-Strained Ge Layers. Japanese Journal of Applied Physics, 2009, 48, 04C130.	0.8	23
31	Development of epitaxial growth technology for Ge1â^'Sn alloy and study of its properties for Ge nanoelectronics. Solid-State Electronics, 2013, 83, 82-86.	0.8	23
32	Experimental observation of type-I energy band alignment in lattice-matched Ge1â^'xâ^'ySixSny/Ge heterostructures. Applied Physics Letters, 2016, 108, .	1.5	23
33	Epitaxial formation and electrical properties of Ni germanide/Ge(110) contacts. Thin Solid Films, 2014, 557, 84-89.	0.8	22
34	Stabilized formation of tetragonal ZrO2 thin film with high permittivity. Thin Solid Films, 2014, 557, 192-196.	0.8	22
35	Constructed Ge Quantum Dots and Sn Precipitate SiGeSn Hybrid Film with High Thermoelectric Performance at Low Temperature Region. Advanced Energy Materials, 2022, 12, .	10.2	22
36	Non-uniform depth distributions of Sn concentration induced by Sn migration and desorption during GeSnSi layer formation. Applied Physics Letters, 2015, 106, .	1.5	20

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37	Effect of alcohol sources on synthesis of single-walled carbon nanotubes. Applied Surface Science, 2008, 254, 7697-7702.	3.1	19
38	Formation of high-quality oxide/Ge1â^'xSnx interface with high surface Sn content by controlling Sn migration. Applied Physics Letters, 2014, 105, 122103.	1.5	19
39	Influence of Structural Variation of Ni Silicide Thin Films on Electrical Property for Contact Materials. Japanese Journal of Applied Physics, 2004, 43, 1896-1900.	0.8	18
40	Influence of Sn incorporation and growth temperature on crystallinity of Ge1â^'xSnx layers heteroepitaxially grown on Ge(110) substrates. Thin Solid Films, 2013, 531, 504-508.	0.8	18
41	Growth and characterization of strain-relaxed SiGe buffer layers on Si(001) substrates with pure-edge misfit dislocations. Materials Science in Semiconductor Processing, 2005, 8, 131-135.	1.9	17
42	Strain-relaxation mechanisms of SiGe layers formed by two-step growth on Si(0 0 1) substrates. Applied Surface Science, 2004, 224, 104-107.	3.1	16
43	Improvement of Al2O3/Ge interfacial properties by O2-annealing. Thin Solid Films, 2012, 520, 3397-3401.	0.8	16
44	Density functional study for crystalline structures and electronic properties of Si1â^'xSnxbinary alloys. Japanese Journal of Applied Physics, 2016, 55, 08PE04.	0.8	16
45	Electrical and optical properties improvement of GeSn layers formed at high temperature under well-controlled Sn migration. Materials Science in Semiconductor Processing, 2017, 57, 48-53.	1.9	16
46	Realizing high thermoelectric performance in p-type Si1-x-yGexSny thin films at ambient temperature by Sn modulation doping. Applied Physics Letters, 2020, 117, .	1.5	16
47	Sn diffusion during Ni germanide growth on Ge1â€“xSnx. Applied Physics Letters, 2011, 99, 211905.	1.5	15
48	Impacts of AlGeO formation by post thermal oxidation of Al2O3/Ge structure on interfacial properties. Thin Solid Films, 2014, 557, 282-287.	0.8	15
49	Control of Strain Relaxation Behavior of Ge1-xSnx Layers for Tensile Strained Ge Layers. ECS Transactions, 2010, 33, 205-210.	0.3	14
50	Crystallinity Improvement of Epitaxial Ge Grown on a Ge(110) Substrate by Incorporation of Sn. Applied Physics Express, 2012, 5, 015501.	1.1	14
51	In-situ Ga doping of fully strained Ge1-xSnx heteroepitaxial layers grown on Ge(001) substrates. Thin Solid Films, 2012, 520, 3206-3210.	0.8	14
52	Influence of Ge substrate orientation on crystalline structures of Ge1â^'Sn epitaxial layers. Thin Solid Films, 2014, 557, 159-163.	0.8	14
53	Epitaxial growth and crystalline properties of Ge1â^'â^'Si Sn on Ge(0 0 1) substrates. Solid-State Electronics, 2015, 110, 49-53.	0.8	14
54	Low-temperature crystallization of Ge-rich GeSn layers on Si3N4 substrate. Materials Science in Semiconductor Processing, 2017, 70, 151-155.	1.9	14

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55	High n-type Sb dopant activation in Ge-rich poly-Ge1â^'xSnx layers on SiO2 using pulsed laser annealing in flowing water. Applied Physics Letters, 2018, 112, .	1.5	14
56	Reinforcement of power factor in N-type multiphase thin film of Si1â^'xâ^'yGexSny by mitigating the opposing behavior of Seebeck coefficient and electrical conductivity. Applied Physics Letters, 2021, 119, .	1.5	14
57	Dislocation structures and strain-relaxation in SiGe buffer layers on Si (0 0 1) substrates with an ultra-thin Ge interlayer. Applied Surface Science, 2004, 224, 108-112.	3.1	13
58	Electrical properties of epitaxial NiSi2/Si contacts with extremely flat interface formed in Ni/Ti/Si(001) system. Microelectronic Engineering, 2006, 83, 2272-2276.	1.1	13
59	(Invited) Assessment of Ge1-xSnx Alloys for Strained Ge CMOS Devices. ECS Transactions, 2010, 33, 529-535.	0.3	13
60	Characterization of Shallow- and Deep-Level Defects in Undoped Ge_{1â^'}_xSn_xEpitaxial Layers by Electrical Measurements. ECS Journal of Solid State Science and Technology, 2016, 5, P3082-P3086.	0.9	13
61	EXAFS study of local structure contributing to Sn stability in SiyGe1-y-zSnz. Materials Science in Semiconductor Processing, 2017, 70, 133-138.	1.9	13
62	Self-organized lattice-matched epitaxy of Si1â^'xSnx alloys on (001)-oriented Si, Ge, and InP substrates. Applied Physics Letters, 2017, 111, .	1.5	13
63	Understanding of interface structures and reaction mechanisms induced by Ge or GeO diffusion in Al2O3/Ge structure. Applied Physics Letters, 2013, 103, .	1.5	12
64	Reduction of Schottky barrier height for n-type Ge contact by using Sn electrode. Japanese Journal of Applied Physics, 2014, 53, 04EA06.	0.8	12
65	Growth of 2 inch Si_{0.5}Ge_{0.5}bulk single crystals. Japanese Journal of Applied Physics, 2015, 54, 04DH03.	0.8	12
66	Ferroelectric phase formation for undoped ZrO₂ thin films by wet O₂ annealing. Japanese Journal of Applied Physics, 2020, 59, SMMA04.	0.8	12
67	Strain relaxation of patterned Ge and SiGe layers on Si(0â€‰0â€‰1) substrates. Semiconductor Science and Technology, 2007, 22, S132-S136.	1.0	11
68	Silicide and germanide technology for contacts and gates in MOSFET applications. Thin Solid Films, 2008, 517, 80-83.	0.8	11
69	Mechanical Properties and Chemical Reactions at the Directly Bonded Siâ€“Si Interface. Japanese Journal of Applied Physics, 2009, 48, 011202.	0.8	11
70	Control of strain relaxation behavior of Ge1â^'xSnx buffer layers. Solid-State Electronics, 2011, 60, 84-88.	0.8	11
71	Epitaxial growth and anisotropic strain relaxation of Ge1â^'xSnx layers on Ge(110) substrates. Solid-State Electronics, 2013, 83, 71-75.	0.8	11
72	Effect of Sn atoms on incorporation of vacancies in epitaxial Ge_{1â^'}_xSn_xfilm grown at low temperature. Applied Physics Express, 2014, 7, 021302.	1.1	11

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73	Characterization of locally strained Ge1â^'xSnx/Ge fine structures by synchrotron X-ray microdiffraction. Applied Physics Letters, 2015, 106, .	1.5	11
74	Interfacial reactions of Ti/ and Zr/Si1â^'xGex/Si contacts with rapid thermal annealing. Thin Solid Films, 2000, 373, 73-78.	0.8	10
75	Homogeneous Si0.5Ge0.5 bulk crystal growth as substrates for strained Ge thin films by the traveling liquidus-zone method. Thin Solid Films, 2012, 520, 3279-3282.	0.8	10
76	Low temperature formation of Si1â^'xâ^'yGexSny-on-insulator structures by using solid-phase mixing of Ge1â^'zSnz/Si-on-insulator substrates. Thin Solid Films, 2012, 520, 3288-3292.	0.8	10
77	Robustness of Sn precipitation during thermal oxidation of Ge_{1â^'}_xSn_xon Ge(001). Japanese Journal of Applied Physics, 2014, 53, 08LD04.	0.8	10
78	Reduction of Schottky barrier height at metal/n-Ge interface by introducing an ultra-high Sn content Ge1â^'xSnx interlayer. Applied Physics Letters, 2015, 107, .	1.5	10
79	Epitaxial Ge1-xSnx Layers Grown by Metal-Organic Chemical Vapor Deposition Using Tertiary-butyl-germane and Tri-butyl-vinyl-tin. ECS Solid State Letters, 2015, 4, P59-P61.	1.4	10
80	Effect of in situ Sb doping on crystalline and electrical characteristics of n-type Ge_{1â^'}_xSn_x epitaxial layer. Japanese Journal of Applied Physics, 2016, 55, 04EB13.	0.8	10
81	Publisherâ€™s Note: â€œImpact of hydrogen surfactant on crystallinity of Ge_{1â^'}_xSn_x epitaxial layersâ€• Japanese Journal of Applied Physics, 2015, 54, 059202.	0.8	10
82	Interfacial Reaction Mechanisms in Al₂O₃/Ge Structure by Oxygen Radical Process. Japanese Journal of Applied Physics, 2013, 52, 04CA08.	0.8	9
83	Interface properties of Al₂O₃/Ge structures with thin Ge oxide interfacial layer formed by pulsed metal organic chemical vapor deposition. Japanese Journal of Applied Physics, 2014, 53, 08LD03.	0.8	9
84	Characterization of crystallinity of Ge1â^'xSnx epitaxial layers grown using metal-organic chemical vapor deposition. Thin Solid Films, 2016, 602, 7-12.	0.8	9
85	Formation and characterization of Ge 1â^'xâ^'y Si x Sn y /Ge 1â^'x Sn x /Ge 1â^'xâ^'y Si x Sn y double heterostructures with strain-controlled Ge 1â^'xâ^'y Si x Sn y layers. Materials Science in Semiconductor Processing, 2017, 70, 156-161.	1.9	9
86	Formation of ultra-low resistance contact with nickel stanogermanide/heavily doped n ⁺-Ge_{1â^'x}Sn_x structure. Semiconductor Science and Technology, 2018, 33, 124001.	1.0	9
87	Silicon-based low-dimensional materials for thermal conductivity suppression: recent advances and new strategies to high thermoelectric efficiency. Japanese Journal of Applied Physics, 2021, 60, SA0803.	0.8	9
88	Characterization of Local Strain around Through-Silicon Via Interconnects by Using X-ray Microdiffraction. Japanese Journal of Applied Physics, 2011, 50, 05ED03.	0.8	9
89	Dependence of Electrical Characteristics on Interfacial Structure of Epitaxial NiSi2/Si Schottky Contacts Formed from Ni/Ti/Si System. Japanese Journal of Applied Physics, 2008, 47, 2402-2406.	0.8	8
90	(Invited) GeSn Technology: Impact of Sn on Ge CMOS Applications. ECS Transactions, 2011, 41, 231-238.	0.3	8

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91	Characterization of Local Strain around Through-Silicon Via Interconnects by Using X-ray Microdiffraction. Japanese Journal of Applied Physics, 2011, 50, 05ED03.	0.8	8
92	Control of Interfacial Properties of Al₂O₃/Ge Gate Stack Structure Using Radical Nitridation Technique. Japanese Journal of Applied Physics, 2011, 50, 10PE02.	0.8	8
93	Characterization and Analyses of Interface Structures in Directly Bonded Si(011)/Si(001) Substrates. Japanese Journal of Applied Physics, 2009, 48, 021208.	0.8	7
94	Microstructures in directly bonded Si substrates. Solid-State Electronics, 2009, 53, 837-840.	0.8	7
95	Structural change of direct silicon bonding substrates by interfacial oxide out-diffusion annealing. Thin Solid Films, 2010, 518, S147-S150.	0.8	7
96	Impact of hydrogen surfactant on crystallinity of Ge1â^'xSnxepitaxial layers. Japanese Journal of Applied Physics, 2015, 54, 04DH15.	0.8	7
97	Effect of Sn on crystallinity and electronic property of low temperature grown polycrystalline-Si1â^'â^'Ge Sn layers on SiO2. Solid-State Electronics, 2015, 110, 54-58.	0.8	7
98	Low thermal budget n-type doping into Ge(001) surface using ultraviolet laser irradiation in phosphoric acid solution. Applied Physics Letters, 2016, 108, .	1.5	7
99	Electrical and optical properties improvement of GeSn layers formed at high temperature under well-controlled Sn migration. Materials Science in Semiconductor Processing, 2017, 70, 139-144.	1.9	7
100	Optoelectronic properties of high-Si-content-Ge_{1â^'xâ€“y}Si_xSn _y /Ge_{1â^'x}Sn_x/Ge_{1â^'xâ€“y}Si_xSn_y double heterostructure. Semiconductor Science and Technology, 2018, 33, 124018.	1.0	7
101	Fermi-level pinning at metal/4H-SiC contact induced by SiC x O y interlayer. Japanese Journal of Applied Physics, 2020, 59, SGGD16.	0.8	7
102	No external load measurement strategy for micro thermoelectric generator based on high-performance Si1â^'xâ^'yGexSny film. Journal of Materiomics, 2021, 7, 665-671.	2.8	7
103	Structural Analysis of Si-Based Nanodot Arrays Self-Organized by Selective Etching of SiGe/Si Films. Japanese Journal of Applied Physics, 2011, 50, 08LB11.	0.8	7
104	CoAl Ohmic Contact Materials with Improved Surface Morphology for p-Type 4H-SiC. Materials Science Forum, 2002, 389-393, 885-888.	0.3	6
105	Control of misfit dislocations in strain-relaxed SiGe buffer layers on SOI substrates. Thin Solid Films, 2006, 508, 147-151.	0.8	6
106	Scanning tunneling microscopy observation of initial growth of Sn and Ge1â^'xSnx layers on Ge(001) substrates. Applied Surface Science, 2008, 254, 6048-6051.	3.1	6
107	Novel method to introduce uniaxial tensile strain in Ge by microfabrication of Ge/Si1â^'Ge structures on Si(0 0 1) substrates. Solid-State Electronics, 2009, 53, 1198-1201.	0.8	6
108	Control of Interfacial Properties of Al₂O₃/Ge Gate Stack Structure Using Radical Nitridation Technique. Japanese Journal of Applied Physics, 2011, 50, 10PE02.	0.8	6

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109	Analysis for positions of Sn atoms in epitaxial Ge1â^'xSnx film in low temperature depositions. Thin Solid Films, 2014, 557, 173-176.	0.8	6
110	Formation and characterization of locally strained Ge1â^'Sn /Ge microstructures. Thin Solid Films, 2014, 557, 164-168.	0.8	6
111	Oxygen and germanium migration at low temperature influenced by the thermodynamic nature of the materials used in germanium metal-insulator-semiconductor structures. Applied Physics Letters, 2015, 107, .	1.5	6
112	Mobility Behavior of Polycrystalline Si_{1-<i>x</i>-<i>y</i>}Ge_{<i>x</i>}Sn<sub><i>y&lt Grown on Insulators. Transactions of the Materials Research Society of Japan, 2015, 40, 351-354.	0.2	6
113	Effect of GeO₂ deposition temperature in atomic layer deposition on electrical properties of Ge gate stack. Japanese Journal of Applied Physics, 2016, 55, 08PC05.	0.8	6
114	Growth of ultrahigh-Sn-content Ge_{1â^'}_xSn_xepitaxial layer and its impact on controlling Schottky barrier height of metal/Ge contact. Japanese Journal of Applied Physics, 2016, 55, 04EB12.	0.8	6
115	Si1â^'xGex bulk single crystals for substrates of electronic devices. Materials Science in Semiconductor Processing, 2017, 70, 12-16.	1.9	6
116	Control of Ge_{1â^'xâ^'y}Si_xSn_ylayer lattice constant for energy band alignment in Ge_{1â^'x}Sn_x/Ge_{1â^'xâ^'y}Si_xSn_y Semiconductor Science and Technology, 2017, 32, 104008.	1.0	6
117	Formation of SiC thin films by chemical vapor deposition with vinylsilane precursor. Japanese Journal of Applied Physics, 2018, 57, 01AE08.	0.8	6
118	Operation of thin-film thermoelectric generator of Ge-rich poly-Ge1-x Sn x on SiO2 fabricated by a low thermal budget process. Applied Physics Express, 2019, 12, 051016.	1.1	6
119	Impact of Wet Annealing on Ferroelectric Phase Formation and Phase Transition of HfO₂â€“ZrO₂ System. ACS Applied Electronic Materials, 2021, 3, 2203-2211.	2.0	6
120	Formation of Palladium Silicide Thin Layers on Si(110) Substrates. Japanese Journal of Applied Physics, 2011, 50, 05EA09.	0.8	6
121	Mobility enhancement by mechanical uniaxial stress on 4H-SiC (0001) lateral metal-oxide-semiconductor field-effect-transistor. Japanese Journal of Applied Physics, 2020, 59, SGGD08.	0.8	6
122	Initial growth behaviors of SiGeC in SiGe and C alternate deposition. Materials Science in Semiconductor Processing, 2005, 8, 5-9.	1.9	5
123	Analysis of Microstructures in SiGe Buffer Layers on Silicon-on-Insulator Substrates. Japanese Journal of Applied Physics, 2005, 44, 7356-7363.	0.8	5
124	Initial Growth Process of TiN Films in Ultrahigh-Vacuum Rapid Thermal Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2006, 45, 49-53.	0.8	5
125	Impact of Pt Incorporation on Thermal Stability of NiGe Layers on Ge(001) Substrates. , 2007, , .		5
126	Formation of Palladium Silicide on Heavily Doped Si(001) Substrates Using Ti Intermediate Layer. Japanese Journal of Applied Physics, 2010, 49, 05FA09.	0.8	5

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127	Control of interfacial properties of Pr-oxide/Ge gate stack structure by introduction of nitrogen. Solid-State Electronics, 2011, 60, 70-74.	0.8	5
128	Increase of Si_{0.5}Ge_{0.5} Bulk Single Crystal Size as Substrates for Strained Ge Epitaxial Layers. Japanese Journal of Applied Physics, 2013, 52, 04CH02.	0.8	5
129	Low temperature growth of SiSn polycrystals with high Sn contents on insulating layers. , 2014, , .		5
130	Formation, crystalline structure, and optical properties of Ge1â^'xâ^'ySnxCyternary alloy layers. Japanese Journal of Applied Physics, 2015, 54, 04DH08.	0.8	5
131	Influence of interface structure on electrical properties of NiGe/Ge contacts. Japanese Journal of Applied Physics, 2015, 54, 05EA01.	0.8	5
132	Formation of chemically stable GeO2 on the Ge surface with pulsed metalâ€“organic chemical vapor deposition. Applied Physics Letters, 2015, 106, 062107.	1.5	5
133	(Invited) Growth and Applications of Si_{1-x}Sn_xThin Films. ECS Transactions, 2017, 80, 253-258.	0.3	5
134	Effect of N bonding structure in AlON deposited by plasma-assisted atomic layer deposition on electrical properties of 4H-SiC MOS capacitor. Japanese Journal of Applied Physics, 2018, 57, 01AE06.	0.8	5
135	Dopant behavior in heavily doped polycrystalline Ge_{1â^'}_xSn_xlayers prepared with pulsed laser annealing in water. Japanese Journal of Applied Physics, 2018, 57, 04FJ02.	0.8	5
136	Improved thermoelectric property of B-doped Si/Ge multilayered quantum dot films prepared by RF magnetron sputtering. Japanese Journal of Applied Physics, 2018, 57, 01AF03.	0.8	5
137	Ultra-thin germanium-tin on insulator structure through direct bonding technique. Semiconductor Science and Technology, 2018, 33, 124002.	1.0	5
138	Energy band structure and electrical properties of Ga-oxide/GaN interface formed by remote oxygen plasma. Japanese Journal of Applied Physics, 2018, 57, 06KA05.	0.8	5
139	(Invited) A New Application of Ge_{1â^'x}Sn_x: Thermoelectric Materials. ECS Transactions, 2018, 86, 321-328.	0.3	5
140	Formation and optoelectronic property of strain-relaxed Ge_{1â^'xâ^'y}Si_xSn _y /Ge_{1â^'x}Sn_x/Ge_{1â^'xâ^'y}Si _x Sn_y double heterostructures on a boron-ion-implanted Ge(001) substrate. Japanese Journal of Applied Physics, 2019, 58, SIIB23.	0.8	5
141	Formation of Palladium Silicide Thin Layers on Si(110) Substrates. Japanese Journal of Applied Physics, 2011, 50, 05EA09.	0.8	4
142	Band alignment at interfaces of amorphous Al2O3 with Ge1â^'xSnx- and strained Ge-based channels. Applied Physics Letters, 2014, 104, 202107.	1.5	4
143	Interaction of Sn atoms with defects introduced by ion implantation in Ge substrate. Journal of Applied Physics, 2014, 115, .	1.1	4
144	Formation and crystalline structure of Ni silicides on Si(110) substrate. Japanese Journal of Applied Physics, 2014, 53, 05GA12.	0.8	4

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145	Importance of control of oxidant partial pressure on structural and electrical properties of Pr-oxide films. Thin Solid Films, 2014, 557, 276-281.	0.8	4
146	Formation of epitaxial Hf digermanide/Ge(001) contact and its crystalline properties. Japanese Journal of Applied Physics, 2018, 57, 07MA05.	0.8	4
147	Growth and electrical properties of in situ Sb-doped Ge1âˆ' x Sn x epitaxial layers for source/drain stressor of strained-Ge transistors. Japanese Journal of Applied Physics, 2018, 57, 121303.	0.8	4
148	Alleviation of Fermi level pinning at metal/n-Ge interface with lattice-matched Si _x Ge_{1âˆ'} _x _{âˆ'} _y Sn _y ternary alloy interlayer on Ge. Japanese Journal of Applied Physics, 2018, 57, 060304.	0.8	4
149	Fabrication of Porous Silicon using Photolithography and Reactive Ion Etching (RIE). Materials Today: Proceedings, 2019, 13, 92-96.	0.9	4
150	Impact of byproducts formed on a 4Hâ€“SiC surface on interface state density of Al2O3/4Hâ€“SiC(0001) gate stacks. Applied Physics Letters, 2020, 116, 222104.	1.5	4
151	Lowering of the Schottky barrier height of metal/n-type 4H-SiC contacts using low-work-function metals with thin insulator insertion. Japanese Journal of Applied Physics, 2021, 60, 075503.	0.8	4
152	Crystal structure change in multilayer GeH flakes by hydrogen desorption under ultrahigh vacuum environments. Japanese Journal of Applied Physics, 2022, 61, SC1048.	0.8	4
153	Conductance Oscillations in Hopping Conduction Systems Fabricated by Focused Ion Beam Implantation. Japanese Journal of Applied Physics, 1997, 36, 4046-4048.	0.8	3
154	Influence of Si1âˆ'xGex interlayer on the initial growth of SiGeC on Si(1 0 0). Applied Surface Science, 2004, 224, 117-121.	3.1	3
155	Silicide and Germanide Technology for Contacts and Metal Gates in MOSFET Applications. ECS Transactions, 2007, 11, 197-205.	0.3	3
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157	Effect of Interfacial Reactions in Radical Process on Electrical Properties of Al2O3/Ge Gate Stack Structure. Journal of Physics: Conference Series, 2013, 417, 012001.	0.3	3
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